

## 2 Amp. Surface Mounted Schottky Barrier Rectifier

<p><b>Dimensions in mm.</b></p>	<p><b>CASE:</b> <b>SMB/DO-214AA</b> (Plastic)</p>	<p><b>Voltage</b> 20 V to 60 V</p>	<p><b>Current</b> 2.0 A</p>
<ul style="list-style-type: none"> <li>• Metal Silicon Junction, majority carrier conduction</li> <li>• High current capability, low forward voltage drop</li> <li>• Guardring for overvoltage protection</li> <li>• Low power loss, high efficiency</li> <li>• High surge capability</li> <li>• Plastic material carries U/L recognition 94V-O</li> <li>• Low profile package</li> <li>• Easy pick and place</li> </ul>			

### Maximum Ratings, according to IEC publication No. 134

		<b>FSS22</b>	<b>FSS23</b>	<b>FSS24</b>	<b>FSS25</b>	<b>FSS26</b>
	<b>Marking Code</b>	B1	B2	B3	B4	B5
$V_{RRM}$	Peak recurrent reverse voltage (V)	20	30	40	50	60
$V_{RMS}$	Maximum RMS voltage (V)	14	21	28	35	42
$V_{DC}$	Maximum DC blocking voltage (V)	20	30	40	50	60
$I_{F(AV)}$	Maximum average Forward current.			2 A		
$I_{FSM}$	8.3 ms. peak forward surge current (Jedec Method)			50 A		
$T_j$	Operating temperature range	– 65 to + 125 °C		– 65 to + 150 °C		
$T_{stg}$	Storage temperature range	– 65 to + 150 °C				

### Electrical Characteristics at Tamb = 25 °C

$V_F$	Max. forward voltage drop at $I_F = 2.0 \text{ A}^{(1)}$	0.55 V	0.70 V
$I_R$	Max. Instantaneous reverse current at $V_{RRM}^{(1)}$ Ta = 25 °C	0.5 mA	
	Ta = 100 °C	20 mA	10 mA
$R_{thj-a}$ $R_{thj-l}$		75 °C/W 17 °C/W	

NOTE: Thermal Resistance from junction to lead or to ambient PCB mounted with 5x5 mm copper pads areas.

(1) Pulse test: 300µs pulse width, 1% duty cycle.



